

## 36 EDS Members Elected to the IEEE Grade of Fellow Effective 1 January 2011

**Mark Allen**, Georgia Institute of Technology, Atlanta, GA, USA

*for contributions to micro and nanofabrication technologies for microelectromechanical systems*

**Asen Asenov**, The University of Glasgow, Glasgow, Scotland

*for contributions to the understanding and prediction of semiconductor device variability via modeling and simulation*

**Paul Berger**, The Ohio State University, Columbus, OH, 43210, USA

*for contributions to the understanding, development, and fabrication of silicon-based resonant interband tunneling devices and circuits*

**Karl Bohringer**, University of Washington, Seattle, WA, USA

*for contributions to microelectromechanical systems, parallel and distributed robotic manipulation, and self-assembly*

**Albert Chin**, National Chiao Tung University, Hsinchu, Taiwan, China

*for contributions to high-K dielectrics and metal gate electrodes for complementary metal-oxide semiconductor*

**Jen-Inn Chyi**, National Central University, Jhong-Li, Taiwan

*for contributions to III-V compound semiconductor optoelectronic devices*

**Paul Davis**, Reading, PA, USA

*for development of bipolar integrated circuits*

**Vivek De**, Intel Corporation, Hillsboro, OR, USA

*for contributions to low power microprocessor design*

**Kristin De Meyer**, IMEC, Leuven, Belgium

*for contributions to exploratory complementary metal-oxide semiconductor field-effect transistors*

**Veronique Ferlet-Cavrois**, ESA ESTEC, Noordwijk, The Netherlands

*for contributions to understanding of radiation effects on electronic devices*

**Digh Hisamoto**, Hitachi, Ltd., Kokubunji, Tokyo, Japan

*for contributions to complementary metal-oxide semiconductor devices*

**Mark Itzler**, Princeton Lightwave, Inc., Princeton, NJ, USA

*for leadership in avalanche photodiode technologies*

**Shin'ichiro Kimura**, Hitachi, Ltd., Kokubunji, Tokyo, Japan

*for contributions to advanced stack memory cells for high density dynamic random access memories*

**Thomas Kuech**, University of Wisconsin-Madison, Madison, WI, USA

*for contributions to electronic materials growth for epitaxial devices*

**Kelin Kuhn**, Intel Corporation, Hillsboro, OR, USA

*for contributions to high performance complementary metal-oxide mechanical system device technology for microprocessors*

**Juin Liou**, University of Central Florida, Orlando, FL, USA

*for contributions to development of electrostatic discharge protection of integrated circuits*

**Paolo Lugli**, Technical University of Munich, Munich, Bavaria, Germany

*for contributions to nanostructured materials and devices*

**Eun Kim**, University of Southern California, Los Angeles, CA, USA

*for contributions to microelectromechanical systems*

**Dirk M Klaassen**, NXP Semiconductors, Waalre, The Netherlands

*for contributions to semiconductor device modeling and simulation*

**Santosh Kurinec**, Rochester Institute of Technology, Rochester, NY, USA

*for leadership in integrating innovative microelectronics research in engineering education*

**Jianqiang Lu**, Rensselaer Polytechnic Institute, Troy, NY, USA

*for contributions to three-dimensional integrated circuit technology*

**Joseph Lyding**, University of Illinois at Urbana-Champaign, Urbana, IL, USA

*for contributions to nanofabrication and metal-oxide semiconductor transistor reliability*

**Chris Mack**, University of Texas at Austin, Austin, TX, USA

*for contributions to semiconductor microlithography*

**Vladimir Mitin**, University at Buffalo, SUNY, Buffalo, NY, USA

*for contributions to sensors and detectors*

**Ken O**, University of Texas, Dallas, Richardson, TX, USA

*for contributions to ultra-high frequency complementary metal-oxide semiconductor circuits*

**Ioannis (John) Papapolymerou**, Georgia Institute of Technology, Atlanta, GA, USA

*for contributions to flexible, microwave and wireless components and systems*

**Robert Puers**, Katholieke Universiteit Leuven, Leuven, Belgium

*for contributions to implantable microelectromechanical systems*

**Johann Reithmaier**, University of Kassel, Kassel, Germany

*for research in active semiconductor nanostructures*

**Elyse Rosenbaum**, University of Illinois at Urbana-Champaign, Urbana, IL, USA  
*for contributions to electrostatic discharge reliability of integrated circuits*

**Gurtej Sandhu**, Micron Technology, Inc., Boise, ID, USA  
*for leadership in development of silicon complementary metal-oxide semiconductor process technology for semiconductor memory devices*

**James Stathis**, IBM Thomas J. Watson Research Center, Yorktown Heights, NY, USA  
*for contributions to complementary metal-oxide semiconductor gate-oxide reliability*

**Tuviah Schlesinger**, Carnegie Mellon University, Pittsburgh, PA, USA  
*for contributions to electro-optic devices and heat-assisted magnetic recording*

**Rama Venkatasubramanian**, RTI International, Research Triangle Park, NC, USA  
*for contributions to nanoscale thermoelectric technologies for thermal management*

**Jeffrey Welser**, IBM Almaden Research Center, San Jose, CA, USA  
*for leadership in emerging device technologies for computer applications*

**Jie Xue**, Cisco Systems, Inc., San Ramon, CA, USA  
*for leadership in electronics packaging technology*

**Kevin Zhang**, Intel Corporation, Portland, OR, USA  
*for contributions to static random access memory for high-performance microprocessors*

Ilesanmi Adesida  
2010 EDS Fellows Chair  
University of Illinois  
Urbana-Champaign, IL, USA